(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
26 May 2005 (26.05.2005)

PCT

(10) International Publication Number
WO 2005/048339 A1

(51) International Patent Classification[7]: H01L 21/336, 29/786

(21) International Application Number: PCT/US2004/033251

(22) International Filing Date: 8 October 2004 (08.10.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/699,887 4 November 2003 (04.11.2003) US

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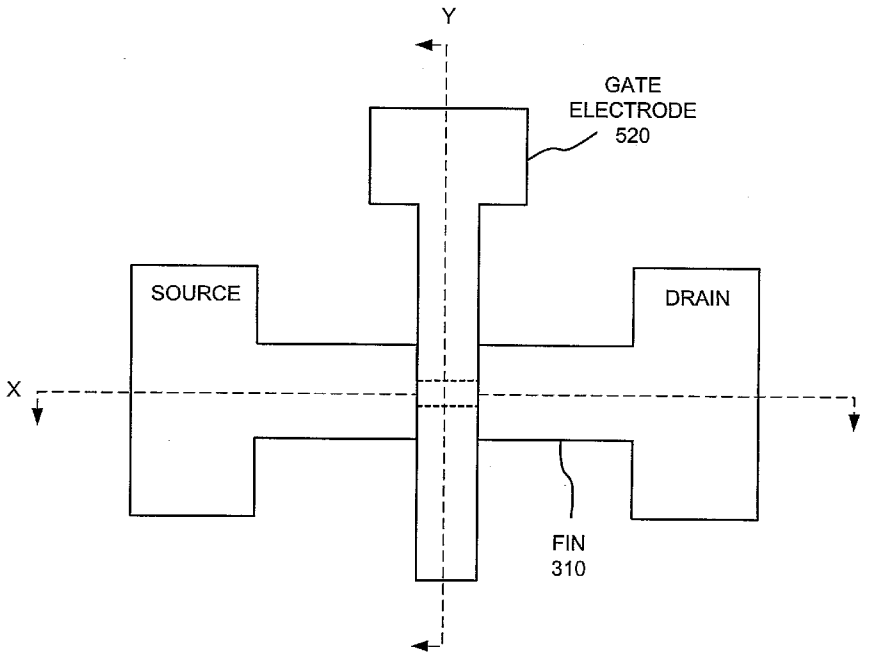
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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,

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(54) Title: SELF ALIGNED DAMASCENE GATE



(57) Abstract: A method for forming a metal-oxide semiconductor field-effect transistor (MOSFET) (200) includes patterning a fin area, a source region, and a drain region on a substrate, forming a fin (310) in the fin area, and forming a mask (320) in the fin area. The method further includes etching the mask (320) to expose a channel area (330) of the MOSFET (200), etching the fin (310) to thin a width of the fin (310) in the channel area (330), forming a gate over the fin (310), and forming contacts to the gate, the source region, and the drain region.

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TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) **Designated States** *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

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